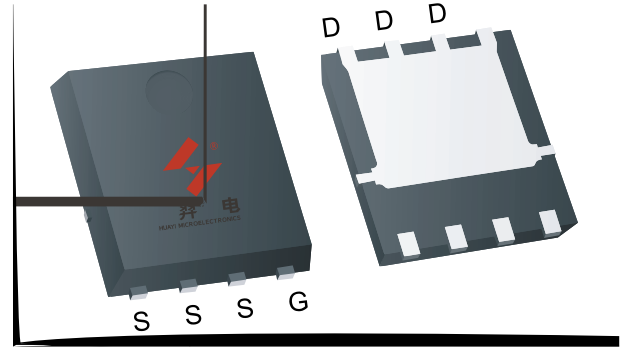


N-Channel Enhancement Mode MOSFET

Feature

- 80V/185A
 $R_{DS(ON)} = 2.4\ m\ (\text{typ.}) @ V_{GS} = 10V$
- 100% Avalanche Tested
- 100% DVDS
- Reliable and Rugged
- Halogen Free and Green Devices Available
 (RoHS Compliant)

Pin Description



Applications

- Switching application
- Li-battery protection
- DC-DC
- Motor control

Ordering and Marking Information

C2 HYG026N08 XYMXXXXXX	Package Code C2: PDFN8L(5x6) Date Code XYMXXXXXX
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Note: HUAYI halogen free products contain molding compounds/die attach materials and 100% matte tin plate Termination finish; which are fully compliant with RoHS. HUAYI halogen free products meet or exceed the halogen free requirements of IPC/JEDEC J-STD-020 for MSL classification at halogen free peak reflow temperature. HUAYI defines "Green" to mean halogen free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage	80	V	
V _{GSS}	Gate-Source Voltage	±20	V	
T _J	Junction Temperature Range	-55 to 175	°C	
T _{STG}	Storage Temperature Range		°C	
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	185	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	400	A
I _D	Continuous Drain Current	Tc=25°C	185	A
		Tc=100°C	130.8	A
P _D	Maximum Power Dissipation	Tc=25°C	211.3	W
		Tc=100°C	105.6	W
R _{θJC}	Thermal Resistance, Junction-to-Case		0.71	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient **		80	°C/W
E _{AS}	Single Pulsed-Avalanche Energy ***	L=0.3mH	551	mJ

Note: * Repetitive rating; pulse width limited by max.junction temperature.
 ** Surface mounted on 1in2 FR-4 board.
 *** Limited by T_{Jmax} , starting T_J=25°C, L = 0.3mH, R_G= 25 , V_{GS} =10V.

Electrical Characteristics(Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG026N08NS1			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	80	-	-	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} =80V, V _{GS} =0V	-	-	1	μA
		T _J =125°C	-	-	10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2.2	3	3.8	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _{DS} =20A	-	2.4	3	m

Electrical Characteristics (Cont.) (Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG026N08NS1			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R_{GS}	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=500KHz$	-	1	-	
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ Frequency=500KHz	-	7940	-	pF
C_{oss}	Output Capacitance		-	1695	-	
C_{rss}	Reverse Transfer Capacitance		-	98	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=40V, R_G=2.5 \Omega,$ $I_{DS}=20A, V_{GS}=10V$	-	23	-	ns
T_r	Turn-on Rise Time		-	34	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	53	-	
T_f	Turn-off Fall Time					

Typical Operating Characteristics

Figure 1: Power Dissipation

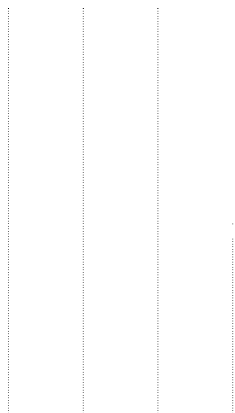


Figure 2: Drain Current

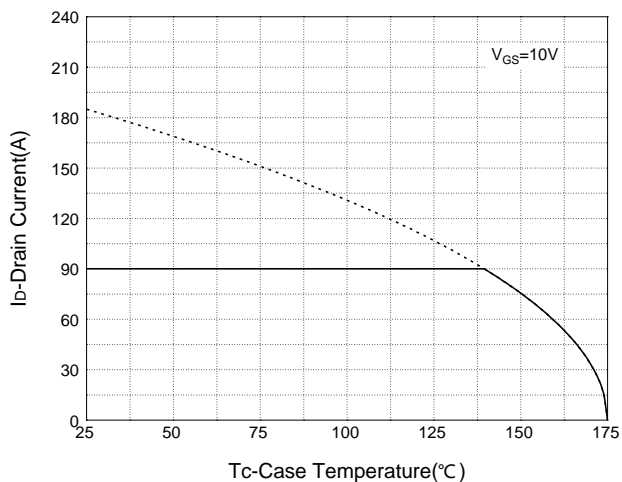


Figure 3: Safe Operation Area

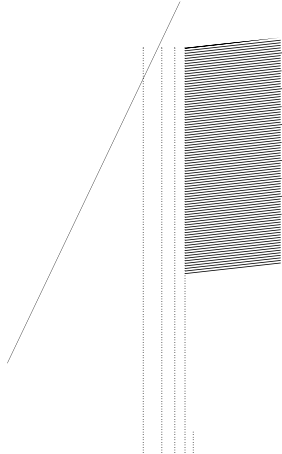


Figure 4: Thermal Transient Impedance

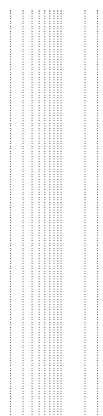


Figure 5: Output Characteristics

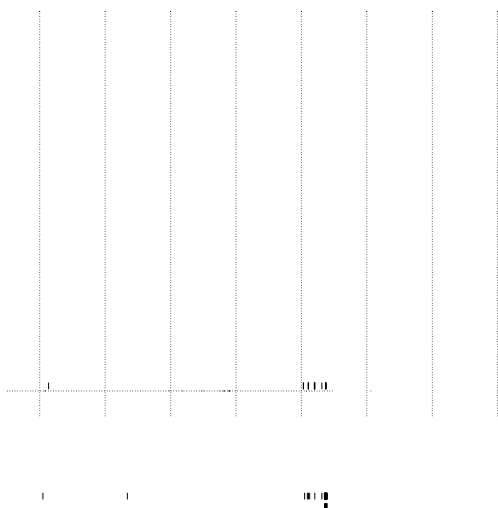
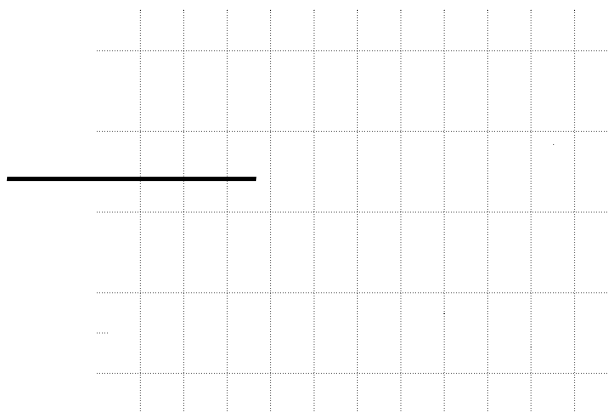


Figure 6: Drain-Source On Resistance



Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

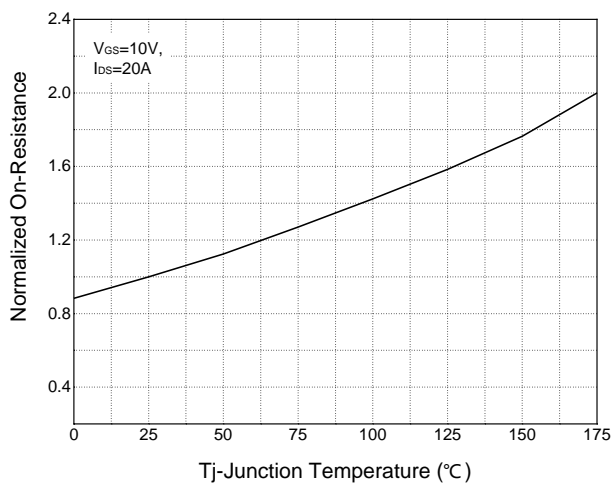


Figure 8: Source-Drain Diode Forward

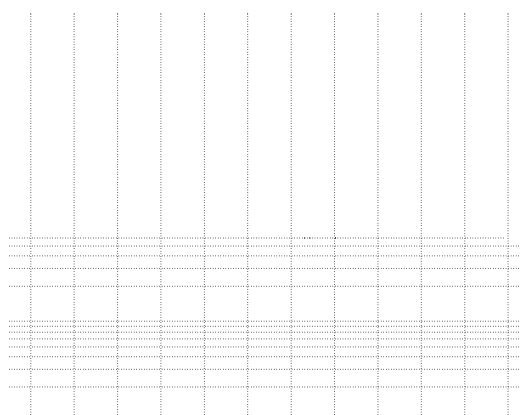
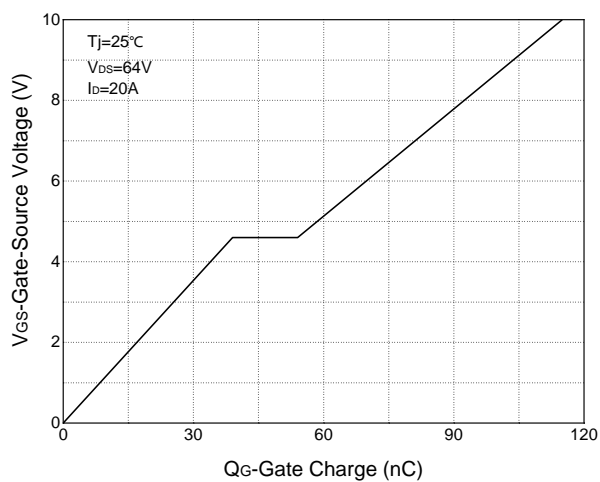


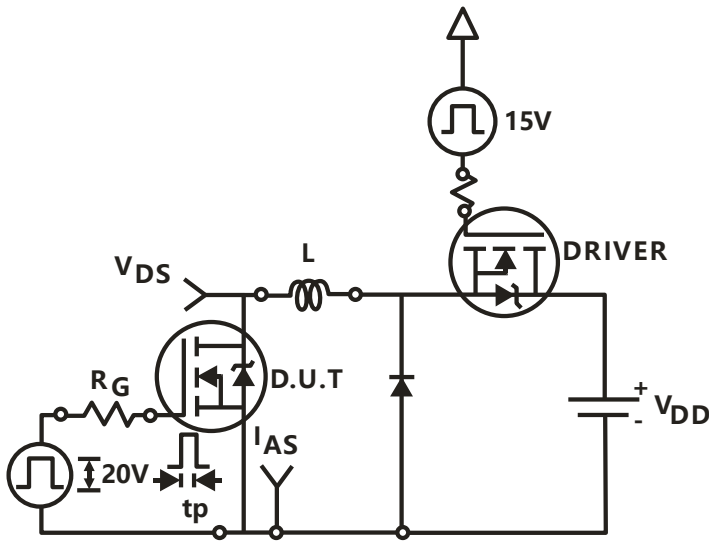
Figure 9: Capacitance Characteristics



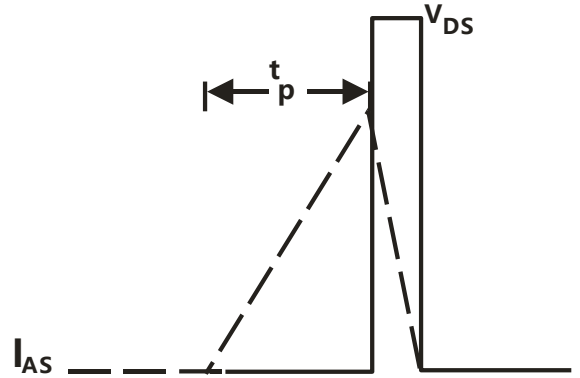
Figure 10: Gate Charge Characteristics



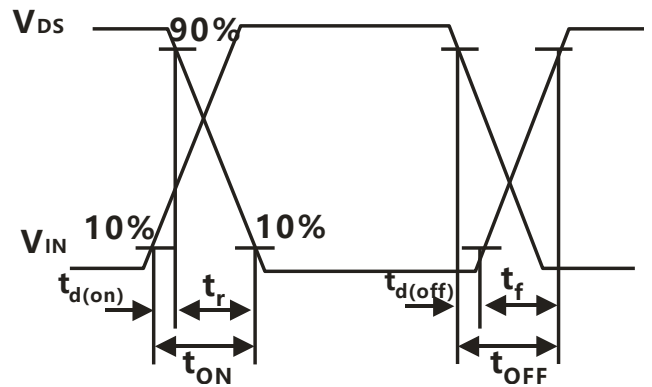
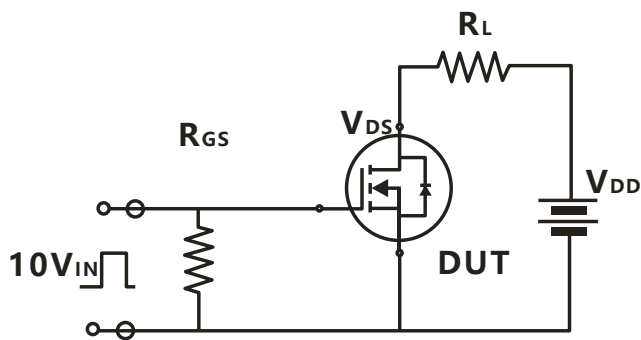
Avalanche Test Circuit



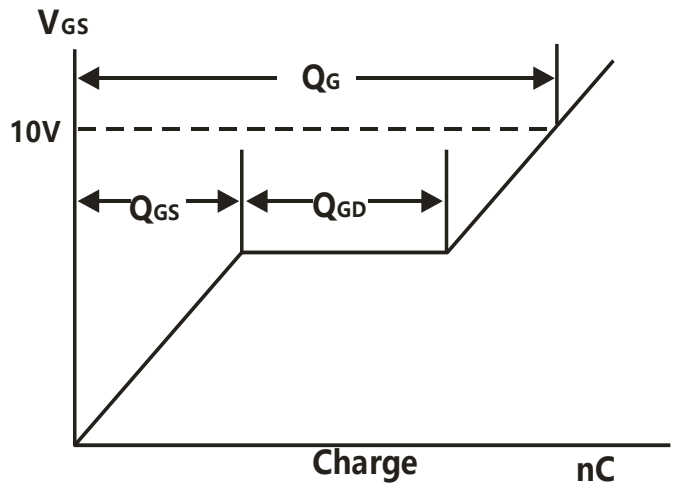
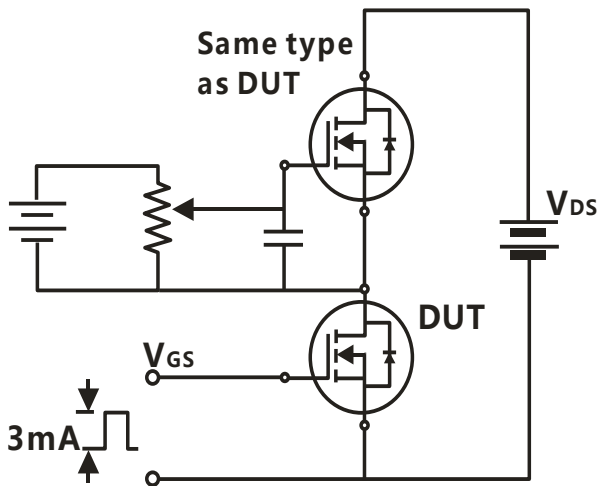
$$E_{AS} = \frac{1}{2} L I_{AS}^2$$



Switching Time Test Circuit



Gate Charge Test Circuit



Device Per Unit

Package Type	Unit	Quantity
PDFN8L(5x6)	Reel	5000

Package Information

PDFN8L(5x6)

(unit:mm)

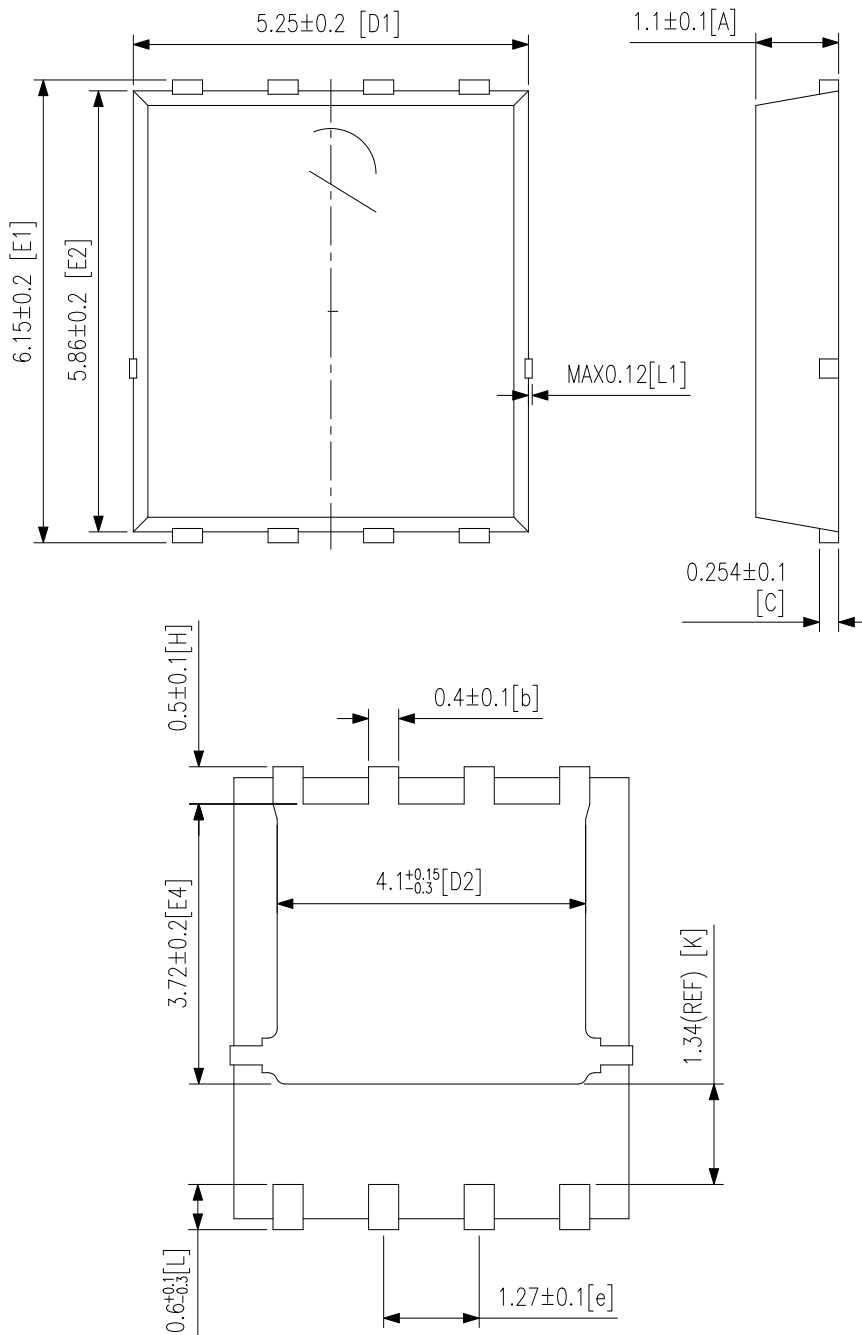


Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168/500 Hrs, Bias @ 150°C
HTGB	JESD-22, A108	168 /500 Hrs, V _{gs} 100% @ 150°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	250/500 Cycles, -55°C~150°C

Customer Service

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